

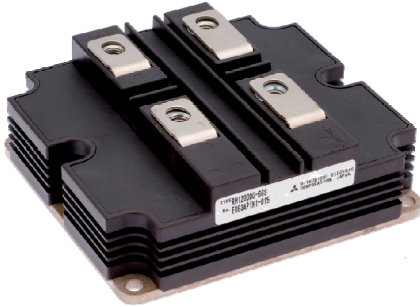
< HIGH VOLTAGE DIODE MODULES >

# RM250DG-130F

HIGH POWER SWITCHING USE  
INSULATED TYPE

High Voltage Diode Modules

**RM250DG-130F**



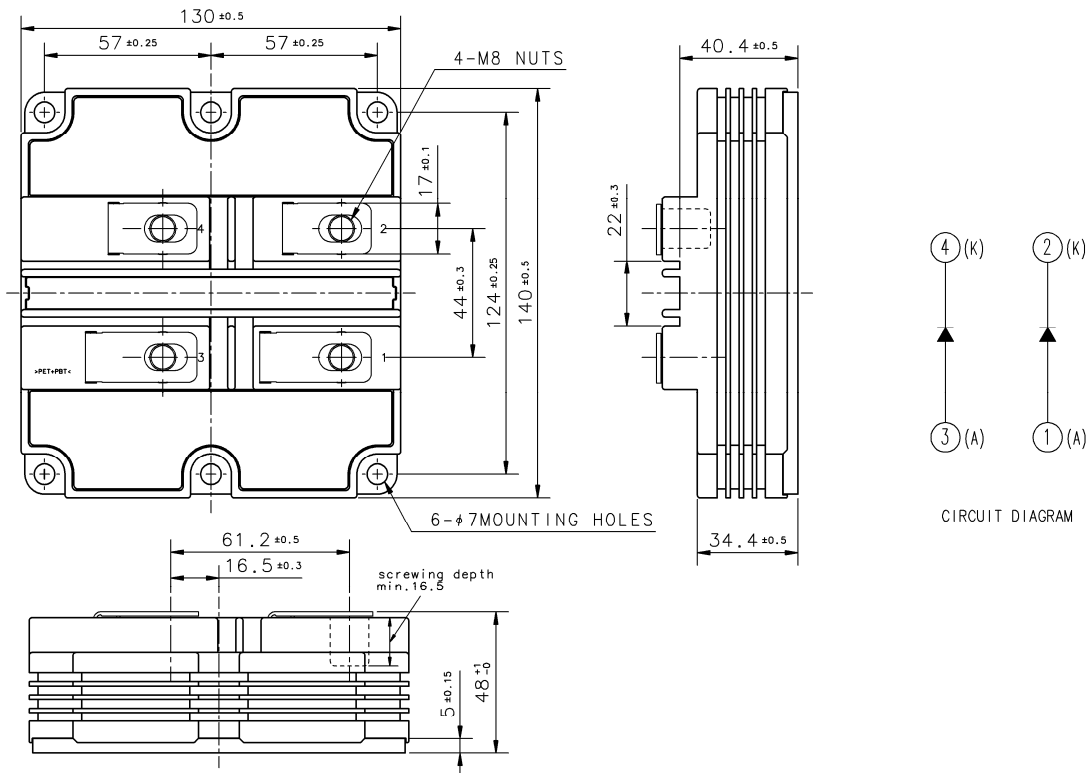
- $I_F$ .....250A
- $V_{RRM}$ .....6500V
- 2-element in a Pack
- High insulated Type
- Soft Recovery Diode
- AISiC Baseplate

**APPLICATION**

Traction drives, High Reliability Converters / Inverters, DC choppers

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



**RM250DG-130F**HIGH POWER SWITCHING USE  
INSULATED TYPE**MAXIMUM RATINGS**

Symbol	Item	Conditions	Ratings	Unit
$V_{RRM}$	Repetitive peak reverse voltage	$T_j = +125^\circ\text{C}$	6500	V
		$T_j = +25^\circ\text{C}$	6300	
		$T_j = -50^\circ\text{C}$	5700	
$V_{RSM}$	Non-repetitive peak reverse voltage	$T_j = +125^\circ\text{C}$	6500	V
		$T_j = +25^\circ\text{C}$	6300	
		$T_j = -50^\circ\text{C}$	5700	
$I_F$	Collector current	DC, $T_c = 65^\circ\text{C}$	250	A
$I_{FRM}$		Pulse <sup>(Note 1)</sup>	500	A
$I_{FSM}$	Surge (non-repetitive) forward current	$T_{Lstart} = 125^\circ\text{C}$ , $t_p = 10$ ms, Half-sine wave, $V_R = 0$ V	2350	A
$I_t^2$	Surge current load integral		28	$\text{kA}^2\text{s}$
$V_{iso}$	Isolation voltage	RMS, sinusoidal, $f = 60$ Hz, $t = 1$ min.	10200	V
$V_e$	Partial discharge extinction voltage	RMS, sinusoidal, $f = 60$ Hz, $Q_{PD} \leq 10$ pC	5100	V
$T_j$	Junction temperature		$-50 \sim +150$	$^\circ\text{C}$
$T_{jop}$	Operating junction temperature		$-50 \sim +125$	$^\circ\text{C}$
$T_{stg}$	Storage temperature		$-55 \sim +125$	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
$I_{RRM}$	Repetitive reverse current	$V_{RM} = V_{RRM}$	$T_j = 25^\circ\text{C}$	—	—	2.0	mA
			$T_j = 125^\circ\text{C}$	—	2.0	10.0	
$V_{FM}$	Forward voltage	$I_F = 250$ A <sup>(Note 2)</sup>	$T_j = 25^\circ\text{C}$	—	3.30	—	V
			$T_j = 125^\circ\text{C}$	—	3.40	4.30	
$t_{rr}$	Reverse recovery time	$V_{CC} = 3600$ V $I_F = 250$ A $L_s = 150$ nH	$T_j = 25^\circ\text{C}$	—	0.55	—	$\mu\text{s}$
			$T_j = 125^\circ\text{C}$	—	0.60	—	
$I_{rr}$	Reverse recovery current	$-d_i/d_t =$ 1250 A/ $\mu\text{s}$ @ $T_j = 25^\circ\text{C}$ 1100 A/ $\mu\text{s}$ @ $T_j = 125^\circ\text{C}$	$T_j = 25^\circ\text{C}$	—	260	—	A
			$T_j = 125^\circ\text{C}$	—	290	—	
$Q_{rr}$	Reverse recovery charge	$-d_i/d_t =$ 1250 A/ $\mu\text{s}$ @ $T_j = 25^\circ\text{C}$ 1100 A/ $\mu\text{s}$ @ $T_j = 125^\circ\text{C}$	$T_j = 25^\circ\text{C}$	—	240	—	$\mu\text{C}$
			$T_j = 125^\circ\text{C}$	—	340	—	
$E_{rec(10\%)}$	Reverse recovery energy <sup>(Note 3)</sup>	Inductive load	$T_j = 25^\circ\text{C}$	—	0.30	—	J
			$T_j = 125^\circ\text{C}$	—	0.60	—	
$E_{rec}$	Reverse recovery energy <sup>(Note 4)</sup>	Inductive load	$T_j = 25^\circ\text{C}$	—	0.40	—	J
			$T_j = 125^\circ\text{C}$	—	0.80	—	

**RM250DG-130F**HIGH POWER SWITCHING USE  
INSULATED TYPE**THERMAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)}$	Thermal resistance	Junction to Case (per 1/2 module)	—	—	75.0	K/kW
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, $\lambda_{grease} = 1 \text{ W/m}^2\text{K}$ $D_{(c-s)} = 100 \mu\text{m}$ (per 1/2 module)	—	48.0	—	K/kW

**MECHANICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$M_t$	Mounting torque	M8 : Main terminals screw	7.0	—	22.0	N·m
$M_s$		M6 : Mounting screw	3.0	—	6.0	N·m
$m$	Mass		—	1.0	—	kg
CTI	Comparative tracking index		600	—	—	—
$d_a$	Clearance		26.0	—	—	mm
$d_s$	Creepage distance		56.0	—	—	mm
$L_{P AK}$	Parasitic stray inductance	1/2 module	—	44.0	—	nH
$R_{AA+KK}$	Internal lead resistance	$T_c = 25^\circ\text{C}$ , 1/2 module	—	0.27	—	mΩ

Note 1. Pulse width and repetition rate should be such that junction temperature ( $T_j$ ) does not exceed  $T_{opmax}$  rating (125°C).

Note 2. Pulse width and repetition rate should be such as to cause negligible temperature rise.

Note 3.  $E_{rec(10\%)}$  is the integral of  $0.1V_R \times 0.1I_F \times dt$ .

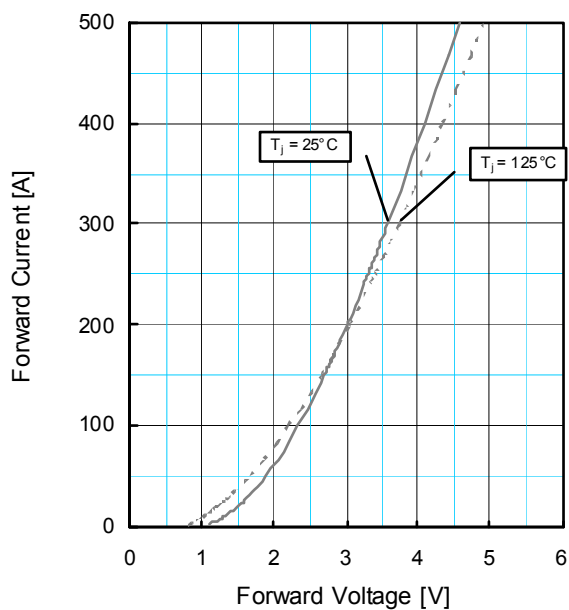
Note 4. The integration range of  $E_{rec}$  according to IEC 60747.

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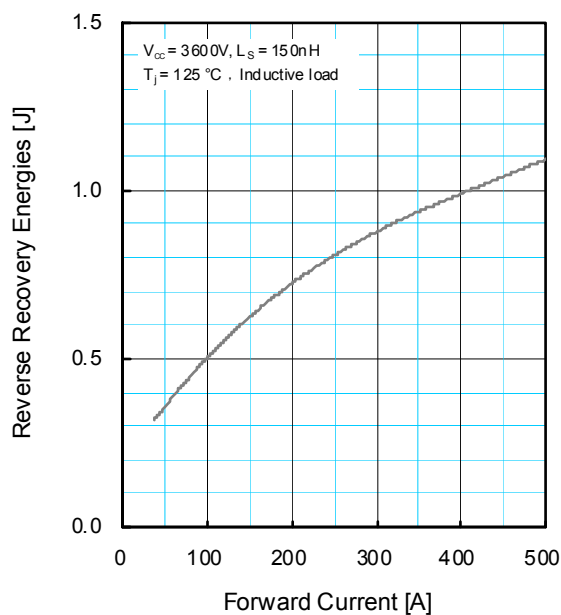
HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

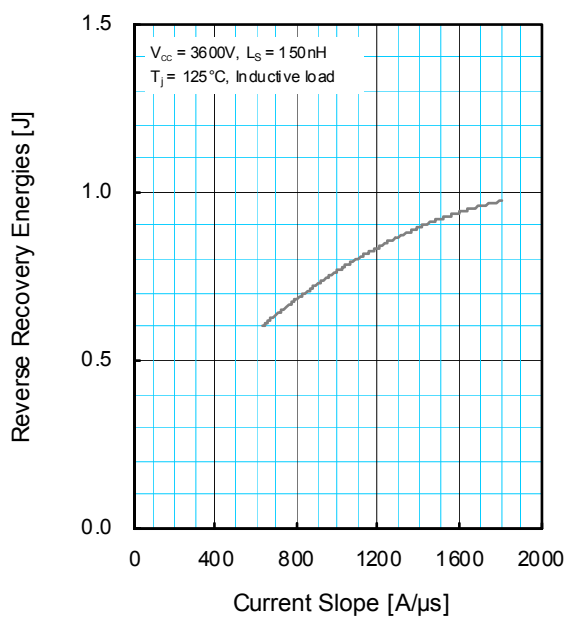
**FORWARD CHARACTERISTICS (TYPICAL)**



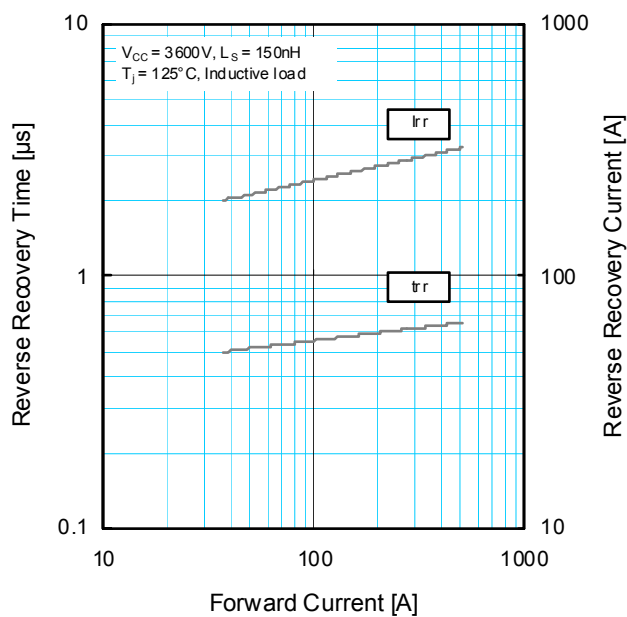
**REVERSE RECOVERY ENERGY CHARACTERISTICS (TYPICAL)**



**REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**



**REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**

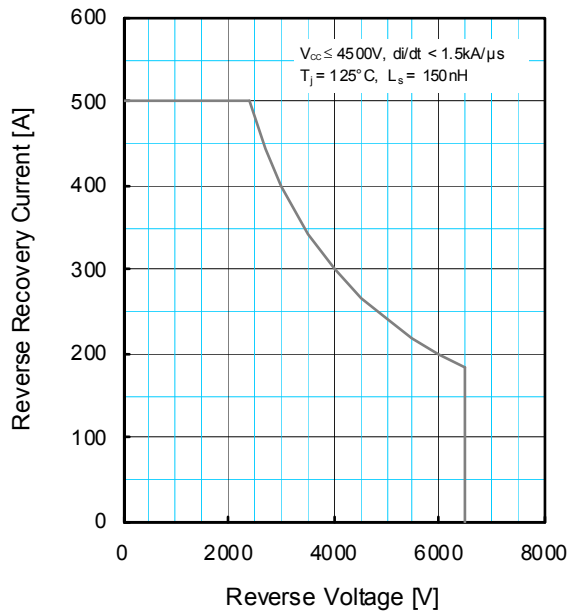


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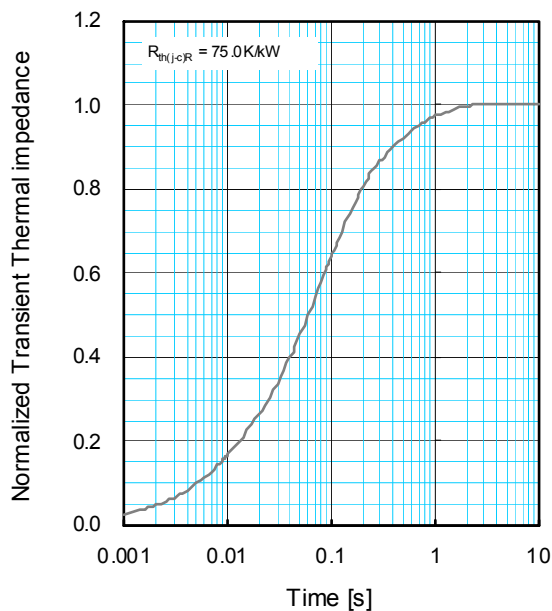
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## PERFORMANCE CURVES

### REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)



### TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
$R_i$ [K/kW]	0.3220	17.0964	32.7254	17.3563
$\tau_i$ [sec]	0.0010	0.01306	0.0859	0.5685

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